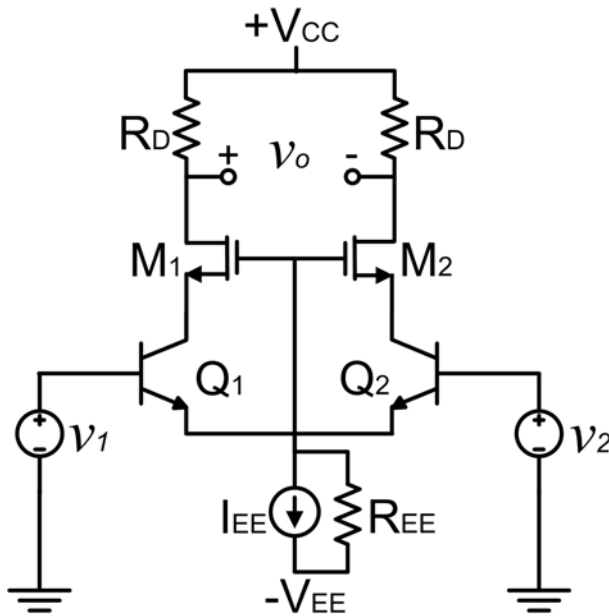


EE311 Analog Electronics #4

Q1) For the differential amplifier given in the figure;



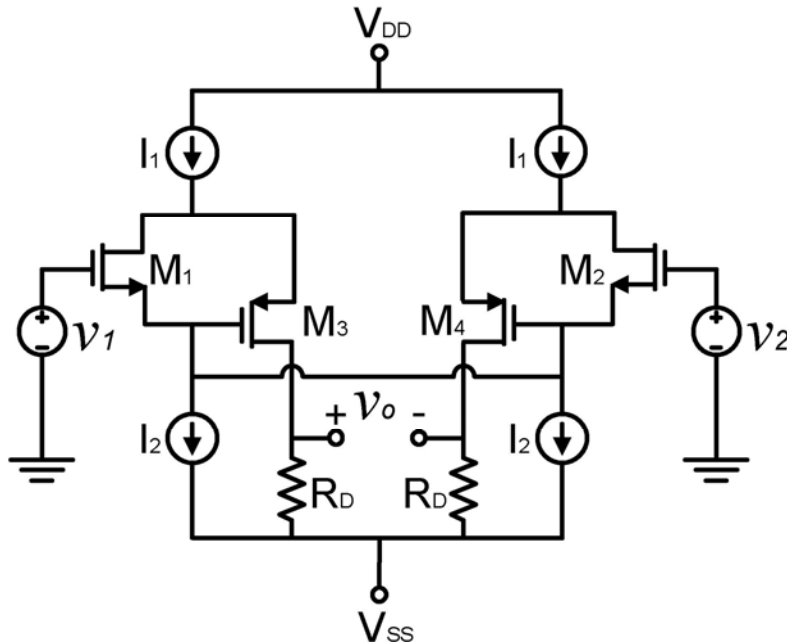
Q₁-Q₂ parameters
 $\beta = 100$
 $V_A = \infty$
 $V_T = 25 \text{ mV}$
 $V_{BE(on)} = 0.7 \text{ V}$

M₁-M₂ parameters
 $K_n = 0.2 \text{ mA/V}^2$
 $V_{TN} = -4 \text{ V}$
 $V_A = \infty$

$V_{CC} = 15 \text{ V}$
 $V_{EE} = 15 \text{ V}$
 $I_{EE} = 100 \mu\text{A}$
 $R_D = 75 \text{ k}\Omega$
 $R_{EE} = 600 \text{ k}\Omega$

- Find the DC values (I_C, V_{CE}) of Q₁ and (I_D, V_{DS}) of M₁ transistors.
- Find the differential-mode gain.
- Find the common-mode gain.
- Find the differential mode input resistance.

Q2) For the differential amplifier given in the figure;



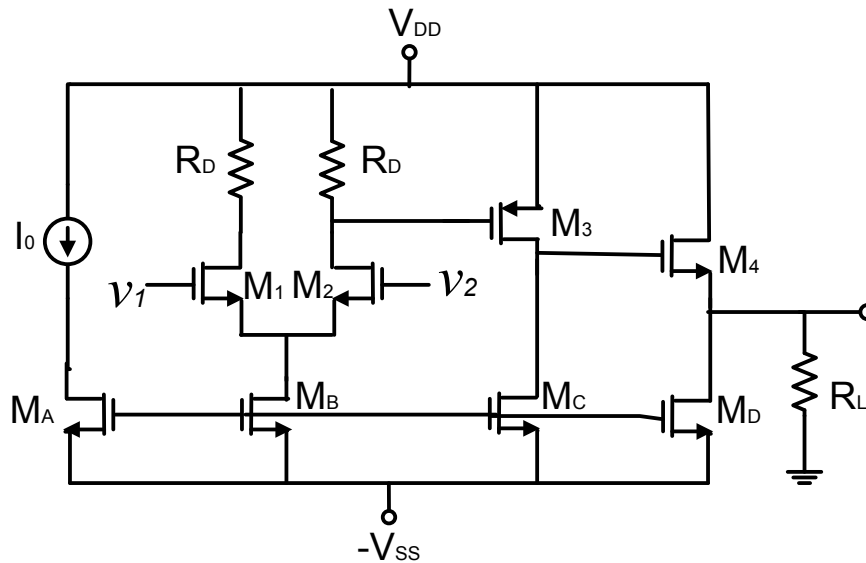
NMOS
 $V_{TN} = 0.75 \text{ V}$
 $\mu_n C_{ox}(W/L) = 1 \text{ mA/V}^2$

PMOS
 $V_{TP} = -0.75 \text{ V}$
 $\mu_p C_{ox}(W/L) = 0.5 \text{ mA/V}^2$

$V_{DD} = 1.5 \text{ V}$
 $V_{SS} = -1.5 \text{ V}$
 $I_1 = 0.2 \text{ mA}$
 $I_2 = 0.1 \text{ mA}$
 $R_D = 10 \text{ k}\Omega$

- Find the DC drain current (I_D) and the small signal parameter g_m of the M_1 and M_3 transistors.
- Draw the small-signal equivalent circuit model for the differential mode.
- Find the differential-mode gain.
- Find the common mode input range, assuming that a minimum voltage drop of 0.1V across the current sources is required.

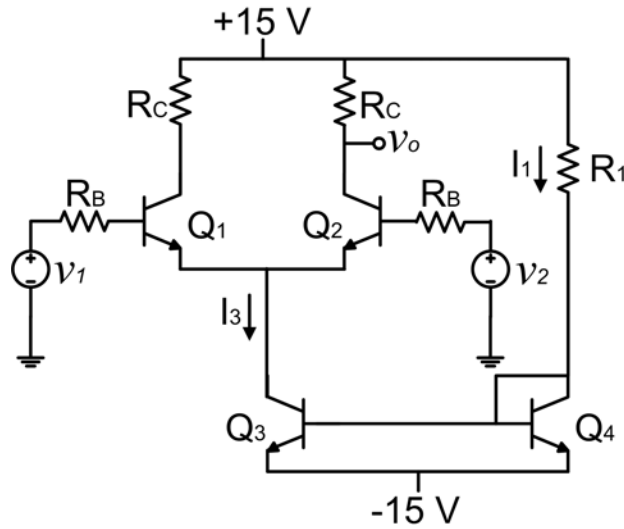
Q3)



$I_0 = 200 \mu\text{A}$
 $K_{nB} = K_{nA}$
 $K_{nC} = 2.5 K_{nA}$
 $K_{nD} = 25 K_{nA}$
 $K_{n1} = K_{n2} = K_{n4} = 5 \text{mA/V}^2$
 $K_{p3} = 2.5 \text{mA/V}^2$
 $V_{tp} = -1 \text{V}$
 $R_L = 2 \text{k}\Omega$
 $r_{oMb} = 375 \text{k}\Omega$
 $r_{oM3} = 200 \text{k}\Omega$
 * The r_o 's for the other transistors are infinitely large.
 * M_A, M_B, M_C, M_D , have same V_t values but different K_n values.

- Calculate the bias current of each transistor in the circuit. Neglect the early effect in DC calculations.
- What is the overall differential mode voltage gain?

Q4) In the BJT differential amplifier in the figure, v_1 and v_2 are AC sources.



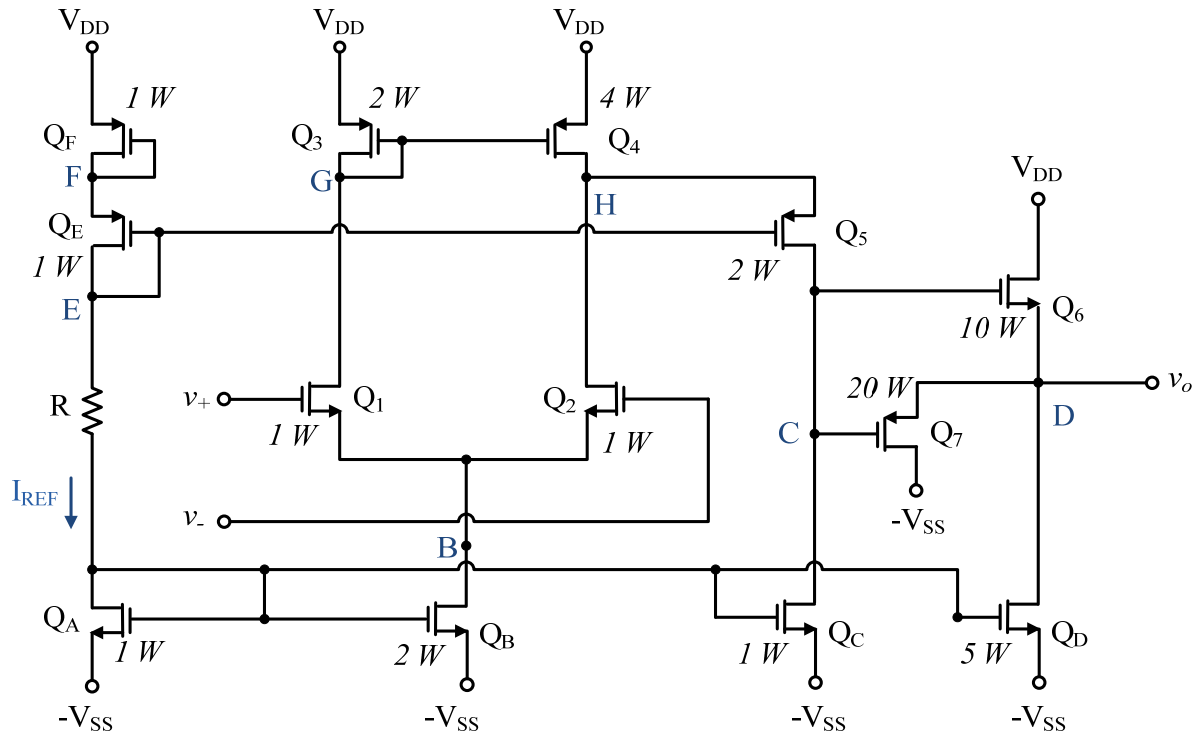
$V_{BE(on)} = 0.7 \text{ V}$
 $\beta = 100$
 $R_B = 10 \text{ k}\Omega$

For Q_1 - Q_2 matched pair:
 $V_A = \infty$

For Q_3 - Q_4 matched pair:
 $V_A = 50 \text{ V}$

- Find the resistance values for R_C and R_1 if $I_3 = 400 \mu\text{A}$ and $V_{CE1} = V_{CE2} = 10 \text{ V}$. Assume $V_A = \infty$ for all transistors in DC calculations. Also neglect the base currents.
- Determine the differential mode gain $A_{dm} = v_o / (v_1 - v_2)$ and the common mode gain $A_{cm} = v_o / v_{cm}$, $v_{cm} = v_1 = v_2$. Draw the half-circuits for the differential mode and the common mode.
- Determine the differential mode input resistance R_{id} and the common mode input resistance R_{icm} .

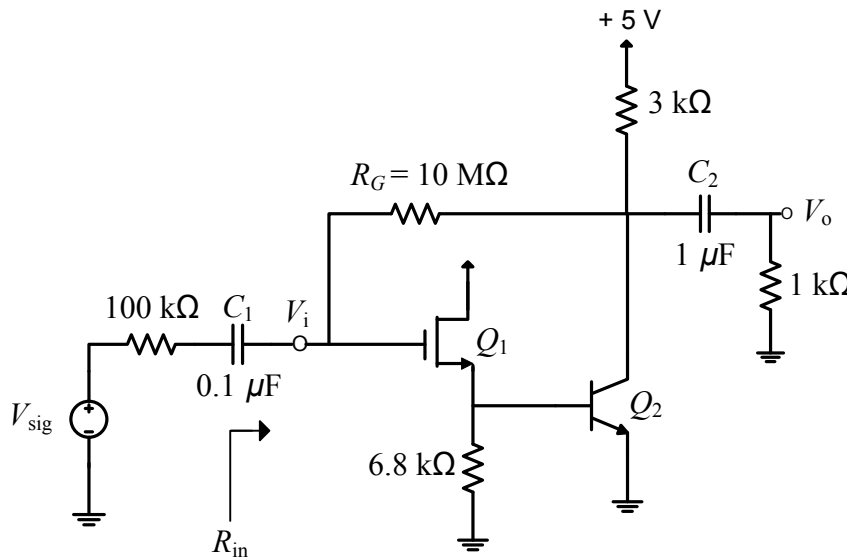
Q5)



For All MOS devices:
 $|V_t| = 1 \text{ V}$
 $\mu_n C_{ox} = 40 \mu\text{A}/\text{V}^2$
 $\mu_p C_{ox} = 20 \mu\text{A}/\text{V}^2$
 $|V_A| = 50 \text{ V}$
 $L = 5 \mu\text{m}$
 $W = 5 \mu\text{m}$
 $V_{DD} = 5 \text{ V}$
 $V_{SS} = 5 \text{ V}$

- Design R to provide a $10 \mu\text{A}$ reference current.
- Calculate the voltage gain $v_o/(v_+ - v_-)$, the input resistance, and the output resistance.
- What is the input common-mode range?
- For what load resistance connected to ground is the output negative voltage limited to -1 V before Q_7 begins to conduct?

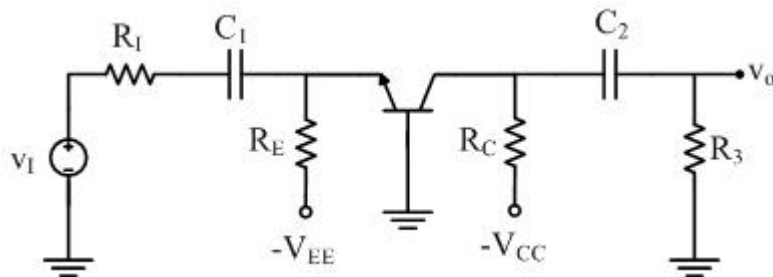
Q6)



BJT
$V_{BE} = 0.7 \text{ V}$
$\beta = 200$
$C_{\mu} = 0.8 \text{ pF}$
$f_T = 600 \text{ MHz}$
NMOS
$V_t = 1 \text{ V}$
$k'_n W/L = 2 \text{ mA/V}^2$
$C_{gs} = C_{gd} = 1 \text{ pF}$

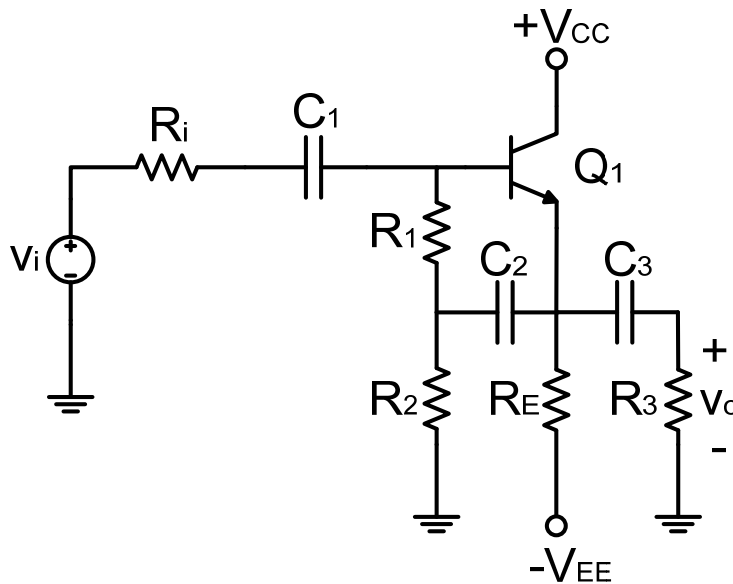
- Consider the dc bias circuit. Neglect the base current of Q_2 in determining the current in Q_1 , find the dc bias currents in Q_1 and Q_2 , and show that they are approximately $100 \mu\text{A}$ and 1 mA respectively.
- Determine the overall voltage gain V_o/V_{sig} .
- Estimate the lower 3-dB frequency, f_L .
- Estimate the higher 3-dB frequency, f_H .
- To considerably reduce the effect of R_G on R_{in} and hence on amplifier performance, consider the effect of adding another $10 \text{ M}\Omega$ resistor in series with the existing one and placing a large bypass capacitor between their joint node and ground. What will R_{in} , A_M and f_H become? Explain briefly.

Q7) Find the upper-cutoff frequency of the common-drain amplifier.



$R_1 = 200 \Omega$
$R_E = 4.3 \text{ k}\Omega$
$R_C = 2.2 \text{ k}\Omega$
$R_3 = 51 \text{ k}\Omega$
$\beta = 100$
$r_x = 300 \Omega$
$f_T = 500 \text{ GHz}$
$C_{\mu} = 0.6 \text{ pF}$
Q-point (1 mA, 5 V)
$r_o = \infty$

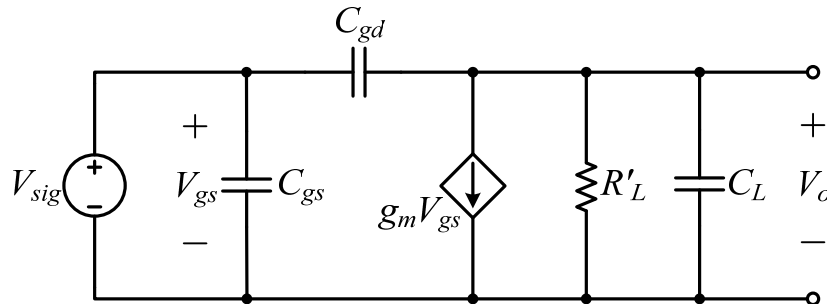
Q8) What are the voltage gain A_V and the maximum input signal amplitude for the amplifier in the figure?



For the BJT, Q_1
 $\beta_F = 100$
 $V_A = 60 \text{ V}$

$R_i = 500 \ \Omega$
 $R_1 = 500 \text{ k}\Omega$
 $R_2 = 500 \text{ k}\Omega$
 $R_3 = 500 \text{ k}\Omega$
 $R_E = 430 \text{ k}\Omega$
 $V_{CC} = 9 \text{ V}$
 $V_{EE} = 9 \text{ V}$

Q9) The figure below shows the equivalent circuit when the CS amplifier is fed with an ideal source V_{sig} having $R_{sig} = 0$. Note that C_L denotes the total capacitance at the output node.



$C_{gd} = 0.5 \text{ pF}$
 $C_L = 2 \text{ pF}$
 $g_m = 4 \text{ mA/V}$
 $R'_L = 5 \text{ k}\Omega$

a) By writing a node equation at the output, show that the transfer function V_o/V_{sig} is given by

$$\frac{V_o}{V_{sig}} = -g_m R'_L \frac{1 - s(C_{gd}/g_m)}{1 + s(C_L + C_{gd})R'_L}$$

b) At frequencies $\omega \ll (g_m/C_{gd})$, the s term in the numerator can be neglected. In such case, what is the upper 3-dB frequency resulting? Compute the values of A_m and f_H .